

**AMENDMENTS TO THE CLAIMS:**

Please amend the claims as follows:

1-6. (Cancelled).

7. (Previously presented) A polishing method which is part of a method for fabricating a semiconductor device, the fabrication method including the process step of polishing a substrate using CMP,

wherein in the polishing process step, a tube-type slurry supply pump is used for supplying a slurry, and

wherein in the tube-type slurry supply pump, a tube which substantially does not contain fine particles for reinforcing the strength of the tube is used as a tube for supplying the slurry, and

wherein the tube is a vinyl chloride type tube.

8. (Cancelled)

9. (Previously presented) A method for fabricating a semiconductor device, comprising the polishing method of claim 7.

10. (Currently amended) A system for polishing a substrate using CMP, comprising:  
a CMP apparatus for polishing the substrate; and  
a tube-type slurry supply pump containing a tube for supplying a slurry during polishing,  
wherein ~~a tube for the tube-type slurry supply pump is a tube in which~~ at least [[the]] an  
inner surface of the tube is formed of a vinyl chloride material, ~~and~~  
~~wherein the tube is a vinyl chloride type tube.~~

11-16. (Cancelled)

17. (Currently amended) A device formation method comprising the steps of:  
placing a substrate in a CMP unit,  
supplying a slurry on the substrate via a tube by a tube-type slurry supply pump through a  
~~tube connected to a slurry pump~~, and  
polishing the substrate on which the slurry is supplied,  
wherein ~~the tube has~~ at least an inner surface of the tube is formed of a vinyl chloride  
material.

18. (Currently amended) The device formation method of claim 17, ~~A device formation~~  
~~method comprising of~~,  
~~placing a substrate in a CMP unit~~,  
~~supplying a slurry on the substrate through a tube connected to a slurry pump~~, and  
~~polishing the substrate on which the slurry is supplied~~,  
wherein the tube is substantially formed of a vinyl chloride material ~~type tube~~.

19. (Currently amended) The system for polishing a substrate using CMP of claim 10,  
~~A system for forming a semiconductor device comprising~~:  
~~a CMP unit for polishing a substrate~~;  
~~a slurry pump for supplying a slurry to the CMP unit~~; and  
~~a tube connected between the CMP unit and the slurry pump~~,  
wherein the tube is substantially formed of a vinyl chloride material ~~type tube~~.

20-21. (Cancelled)

22. (New) A polishing method of claim 7,  
wherein the tube is repeatedly compressed by the tube-type slurry supply pump.
23. (New) A method for fabricating a semiconductor device of claim 9,  
wherein the tube is repeatedly compressed by the tube-type slurry supply pump.
24. (New) A system for polishing a substrate using CMP of claim 10,  
wherein the tube is repeatedly compressed by the tube-type slurry supply pump.
25. (New) A device formation method of claim 17,  
wherein the tube is repeatedly compressed by the tube-type slurry supply pump.
26. (New) A polishing method of claim 7,  
wherein a delivery roller repeatedly compresses the tube in the tube-type slurry supply  
pump.
27. (New) A method for fabricating a semiconductor device of claim 9,  
wherein a delivery roller repeatedly compresses the tube in the tube-type slurry supply  
pump.
28. (New) A system for polishing a substrate using CMP of claim 10,  
wherein a delivery roller repeatedly compresses the tube in the tube-type slurry supply  
pump.
29. (New) A device formation method of claim 17,  
wherein a delivery roller repeatedly compresses the tube in the tube-type slurry supply  
pump.